TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

# **TPC6113**

## Lithium Ion Battery Applications

#### **Power Management Switch Applications**

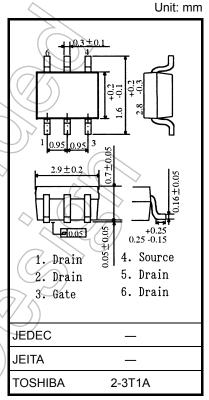
- Small footprint due to small and thin package
- Low drain-source ON-resistance:  $RDS(ON) = 38 \text{ m}\Omega \text{ (typ.)}$

$$(V_{GS} = -4.5V)$$

- Low leakage current:  $IDSS = -10 \mu A (max) (VDS = -20 V)$
- Enhancement mode:  $V_{th} = -0.5$  to -1.2 V ( $V_{DS} = -10$  V,  $I_{D} = -0.2$  mA)

### **Absolute Maximum Ratings (Ta = 25°C)**

Characte	ristics	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-20	V
Drain-gate voltage (R	GS = 20 kΩ)	$V_{DGR}$	-20	À
Gate-source voltage		V <sub>GSS</sub>	<u>+</u> 12	> v
Drain current	DC (Note 1)	I <sub>D</sub>	_5	А
Drain current	Pulse (Note 1)	I <sub>DP</sub>	-20	A
Drain power dissipation	on (t = 5 s) (Note 2a)	PD	2.2	(w
Drain power dissipation (t = 5 s) (Note 2b)		PD	0.7	W
Single pulse avalanch	e energy (Note 3)	EAS	1.6	mJ
Avalanche current		(I <sub>AR</sub> )	-2.5	A
Channel temperature	((	7) (ch	150	°C
Storage temperature	range	T <sub>stg</sub>	-55 to 150	→°C



Weight: 0.011 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated/failure rate, etc).

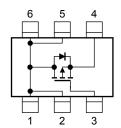
#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t = 5 \text{ s})$ (Note 2a)	R <sub>th (ch-a)</sub>	56.8	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	R <sub>th (ch-a)</sub>	178.5	°C/W

Note: (Note 1), (Note 2), (Note 3): See other pages.

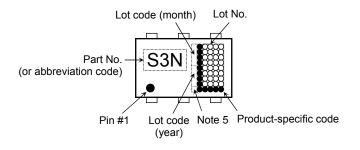
This transistor is an electrostatic-sensitive device. Please handle with caution.

#### **Circuit Configuration**



Start of commercial production 2009-11

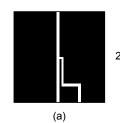
#### Marking (Note 4)



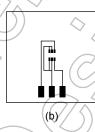
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)

(b) Device mounted on a glass-epoxy board (b) (t = 5 s)



 $FR-4 \\ 25.4 \times 25.4 \times 0.8 \\ \text{(Unit: mm)}$ 



25.4 × 25.4 × 0.8 (Unit: mm)

Note 3:  $V_{DD} = -16 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 0.2 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = -2.5 \text{ A}$ 

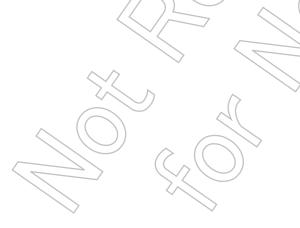
Note 4: • on lower left of the marking indicates Pin 1.

Note 5: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



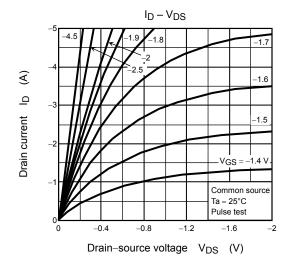
### **Electrical Characteristics (Ta = 25°C)**

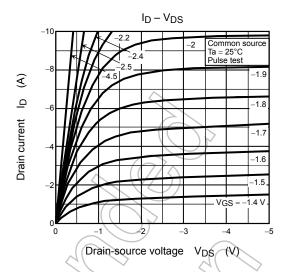
Cha	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cut-off curr	ent	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$		_	-10	μА	
Drain-source breakdown voltage		V <sub>(BR) DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-20 — -		_	V	
		V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 8 \text{ V (Note 6)}$	-12	_	_	V	
Gate threshold voltage		$V_{th}$	$V_{DS} = -10 \text{ V}, I_D = -0.2 \text{ mA}$	-0.5	)/_	-1.2	V	
Drain-source ON-resistance		R <sub>DS</sub> (ON)	$V_{GS} = -2.5 \text{ V}, I_D = -2.5 \text{ A}$	77	56	85	mO	
		R <sub>DS</sub> (ON)	$V_{GS} = -4.5 \text{ V}, I_D = -2.5 \text{ A}$	$\rightarrow$	38	55	mΩ	
Input capacitance		C <sub>iss</sub>			690	_		
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	93	_	pF	
Output capacitance		Coss		_	117	_		
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> 0 V   I <sub>D</sub> = -2.5 A	- (	6	<u> </u>		
	Turn-on time	t <sub>on</sub>	VGS _5 V VOUT	(	13	) —	no	
	Fall time	t <sub>f</sub>	7. y w o G	7	25	_	ns	
	Turn-off time	t <sub>off</sub>	$V_{DD} \approx -10 \text{ V}$ Duty $\leq 1\%$ , $t_W = 10 \mu\text{s}$		81	_		
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ -16 V, V <sub>GS</sub> = -5 V,	) _	10	_		
Gate-source charge 1		Q <sub>gs1</sub>	ID = -5 A	_	1.3	_	nC	
Gate-drain ("miller") charge		$Q_{gd}$		_	2.8	_		

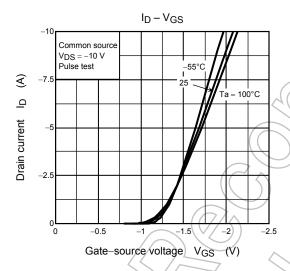
## Source-Drain Ratings and Characteristics (Ta = 25°C)

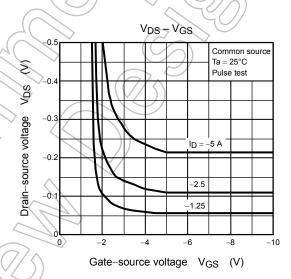
Charact	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	IDRP	$\langle \langle \rangle \rangle$	_	_	-20	Α
Forward voltage	(diode)	V <sub>DSF</sub>	$I_{DR} = -5 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

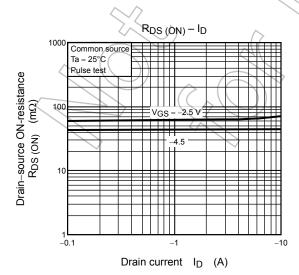
Note 6: VDSX mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.



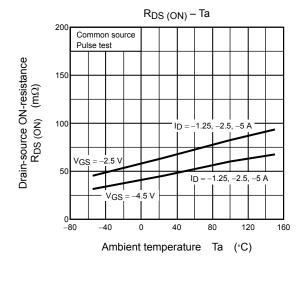


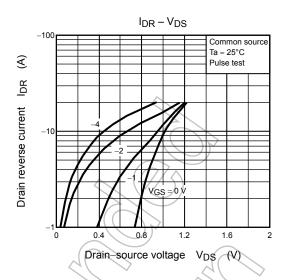


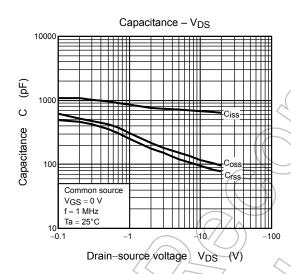


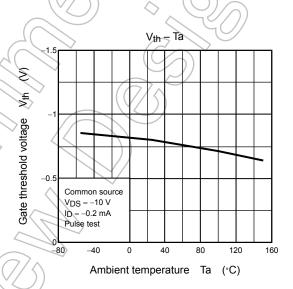


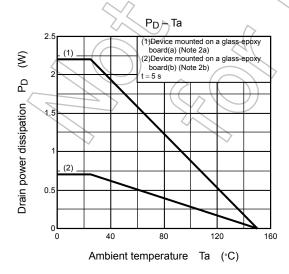
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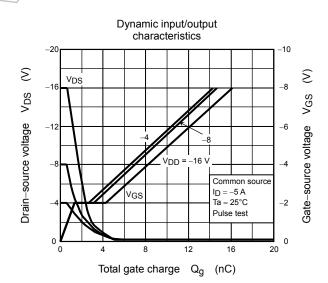




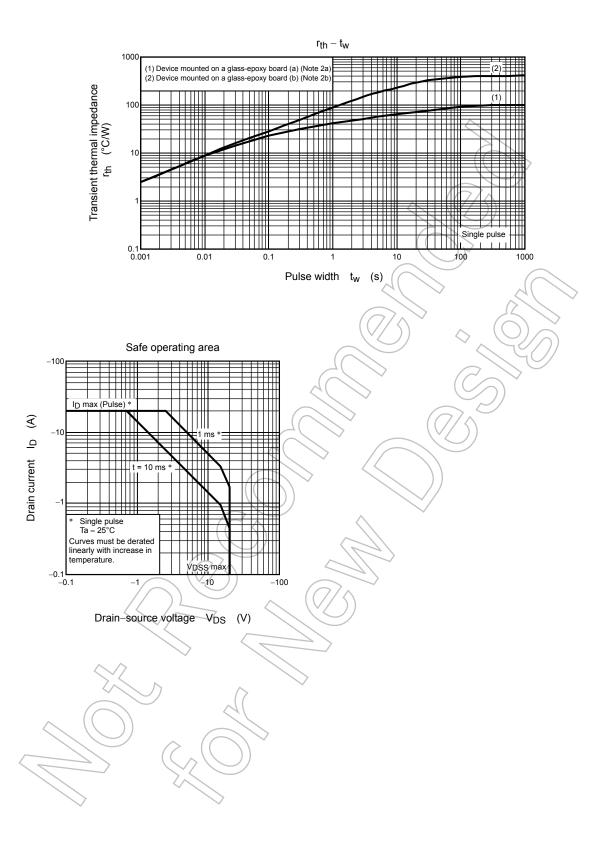








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